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Substitute for form 1449A/PTO		Complete if Known				
			Application Number	09/938,399		
INFO	PRMATION	DISCLOSURE	Filing Date	August 23, 2001		
STA	TEMENT B'	Y APPLICANT	First Named Inventor	Barnes, Michael		
			Group Art Unit			
(use as many sheets as necessary)		Examiner Name				
Sheet	1	of	Attorney Docket Number	016301-039900US		

			U.S. PATENT DOCUM	MENTS	
Examiner Initials *	Cite No.¹	U.S. Patent Document  Kind Code <sup>2</sup> Number  (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
W	AA	5,413,671	Ketchum	05-09-1995	
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FOREIGN PATENT DOCUMENTS								
Examiner Initials*	Cite No.1	Foreign Patent Document  Office <sup>3</sup> Number <sup>4</sup> Kind Code <sup>5</sup>		ocument Kind Code <sup>5</sup>	Name of Patentee or Applicant of	Date of Publication of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant	т6
		1	1	(if known)	Cited Document	MM-DD-YYYY	Figures Appear	T°
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	AW							
	AX							
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Examiner Signature	Kllooce	Date Considered	101	21/02

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<sup>&</sup>lt;sup>1</sup> Unique citation designation number. <sup>2</sup> See attached Kinds of U.S. Patent Documents. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). 4 For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

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tute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Complete if Known **Application Number** 09/938,399 Filing Date August 23, 2001 First Named Inventor Barnes, Michael Group Art Unit **Examiner Name** 

(use as many sheets as necessary)

Sheet of Attorney Docket Number 016301-039900US

	•	OTHER PRIOR ART NON PATENT LITERATURE DOCUMENTS			
Examiner Initials *	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²		
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	ВА	ROY G. GORDON, et al., "Silicon Dimethylamido Complexes and Ammonia as Precursors for the Atmospheric Pressure Chemical Vapor Deposition of Silicon Nitride Thin Films", Chem. Mater., (1990), pp. 480-482, Vol. 2, No. 5			
	BB	M. L. HAMMOND, "Epitaxial Silicon Reactor Technology – A Review; Part I: Reactor Technology", Solid State Technology, (May 1988), pp. 159-164			
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$\bigvee$	BD	GEERT JANSEN, "Atmospheric Pressure Chemical Vapor Deposition of SiN using Sil4 and NH <sub>3</sub> as precursors", (September 6, 1999), 32 pgs.			
	BE				
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